



### 60V +175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

## **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max                     | I <sub>D</sub> Max<br>T <sub>C</sub> = +25°C |
|-------------------|---|--|
| 60V               | $25m\Omega @ V_{GS} = 10V$                  | 32A  |
| 60 V              | $40 \text{m}\Omega @ V_{GS} = 4.5 \text{V}$ | 25A  |

### **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance making it ideal for high efficiency power management applications.

# **Applications**

- Backlighting
- Power-Management Functions
- DC-DC Converters

### **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- High-Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Low-Input Capacitance
- Fast-Switching Speed
- Wettable Flank for Improved Optical Inspections
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMNH6021SPDWQ)

### **Mechanical Data**

- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed Over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 <sup>®</sup>3
- Weight: 0.097 grams (Approximate)

] D1 ] D1

D2

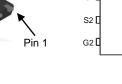
D2



Top View

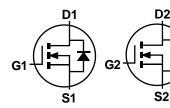


**Bottom View** 



S1 [

G1



**Equivalent Circuit** 

### **Ordering Information** (Note 4)

| Part Number     | Case                         | Packaging          |
|-----------------|------------------------------|--------------------|
| DMNH6021SPDW-13 | PowerDI5060-8 (SWP) (Type R) | 2500 / Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Pin Out

Top View

- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



Oll = Manufacturer's Marking
NH6021DW = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 19 = 2019)
WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



# 

| Characteristic  | Symbol                           | Value          | Unit       |   |
|---|----------------------------------|----------------|------------|---|
| Drain-Source Voltage  | V <sub>DSS</sub>                 | 60             | V          |   |
| Gate-Source Voltage   | V <sub>GSS</sub>                 | ±20            | V          |   |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V                                     | $T_A = +25$ °C<br>$T_A = +70$ °C | I <sub>D</sub> | 8.2<br>6.5 | А |
| Continuous Drain Current (Note 7) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$ |                                  | I <sub>D</sub> | 32<br>22   | А |
| Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)   | I <sub>DM</sub>                  | 80             | А          |   |
| Maximum Continuous Body Diode Forward Current (Note 7)                                      | Is                               | 32             | А          |   |
| Avalanche Current, L = 0.1mH (Note 8)   | I <sub>AS</sub>                  | 35             | Α          |   |
| Avalanche Energy, L = 0.1mH (Note 8)  | E <sub>AS</sub>                  | 64             | mJ         |   |

# Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

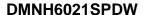
| Characteristic                                   | Symbol         | Value           | Unit        |      |
|--|----------------|-----------------|-------------|------|
| Total Power Dissipation (Note 5)                 | $P_{D}$        | 1.5             | W           |      |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State   | $R_{	hetaJA}$   | 99          | °C/W |
| Thermal Resistance, Junction to Ambient (Note 3) | t<10s          |                 | 53          |      |
| Total Power Dissipation (Note 6)                 |                | $P_{D}$         | 2.8         | W    |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State   | D               | 54          | °C/W |
| Thermal Resistance, Junction to Ambient (Note 6) | t<10s          | $R_{	hetaJA}$   | 27          |      |
| Thermal Resistance, Junction to Case (Note 7)    | $R_{	heta JC}$ | 2.2             | °C/W        |      |
| Operating and Storage Temperature Range          |                | $T_{J,}T_{STG}$ | -55 to +175 | °C   |

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

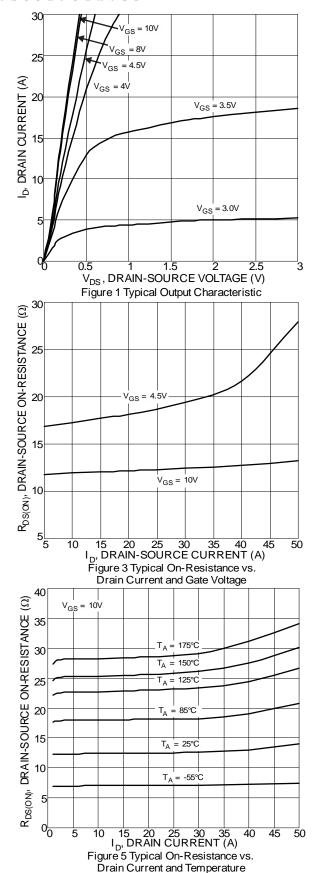
| Characteristic   |                     | Min | Тур   | Max  | Unit | Test Condition   |  |
|--|---------------------|-----|-------|------|------|--|--|
| OFF CHARACTERISTICS (Note 9)                           |                     |     |       |      |      |  |  |
| Drain-Source Breakdown Voltage                         |                     | 60  | _     | _    | V    | $V_{GS} = 0V, I_D = 250\mu A$                            |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C |                     | _   | _     | 1    | μA   | $V_{DS} = 60V$ , $V_{GS} = 0V$                           |  |
| Gate-Source Leakage                                    |                     | _   | _     | ±100 | nA   | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                       |  |
| ON CHARACTERISTICS (Note 9)                            |                     |     |       |      |      |  |  |
| Gate Threshold Voltage                                 | V <sub>GS(TH)</sub> | 1   | _     | 3    | V    | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$                     |  |
| Static Drain-Source On-Resistance                      |                     | _   | 15    | 25   | mΩ   | $V_{GS} = 10V, I_D = 15A$                                |  |
| Static Drain-Source On-Resistance                      | R <sub>DS(ON)</sub> | _   | 21    | 40   |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 12A             |  |
| Diode Forward Voltage                                  | $V_{SD}$            | _   | 0.75  | 1.2  | V    | $V_{GS} = 0V, I_S = 2.6A$                                |  |
| DYNAMIC CHARACTERISTICS (Note 10)                      | •                   |     |       | •    | •    | •  |  |
| Input Capacitance                                      | Ciss                | _   | 1,143 | _    | pF   | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V,<br>f = 1MHz |  |
| Output Capacitance                                     | Coss                | _   | 168   | _    | pF   |  |  |
| Reverse Transfer Capacitance                           | C <sub>rss</sub>    | _   | 69    | _    | pF   |  |  |
| Gate Resistance  | Rg                  |     | 2.5   | _    | Ω    | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$               |  |
| Total Gate Charge (V <sub>GS</sub> = 10V)              | Qg                  |     | 20.1  | _    | nC   |  |  |
| Total Gate Charge (V <sub>GS</sub> = 6V)               |                     |     | 12    | _    | nC   | 7, 20,4 20,4   |  |
| Gate-Source Charge                                     | $Q_{gs}$            | _   | 4.3   | _    | nC   | $V_{DS} = 30V, I_{D} = 20A$                              |  |
| Gate-Drain Charge                                      | $Q_{gd}$            | _   | 5.5   | _    | nC   | 1  |  |
| Turn-On Delay Time                                     | t <sub>D(ON)</sub>  | _   | 4.4   | _    | ns   |  |  |
| Turn-On Rise Time                                      | t <sub>R</sub>      | _   | 6.0   | _    | ns   | $V_{DD} = 30V, V_{GS} = 10V,$                            |  |
| Turn-Off Delay Time                                    | t <sub>D(OFF)</sub> | _   | 14.2  | _    | ns   | $R_g = 4.7\Omega, I_D = 20A$                             |  |
| Turn-Off Fall Time                                     | t <sub>F</sub>      | _   | 5.4   | _    | ns   |  |  |
| Body Diode Reverse Recovery Time                       | t <sub>RR</sub>     | _   | 21.2  | _    | ns   | 1  |  |
| Body Diode Reverse Recovery Charge                     | Q <sub>RR</sub>     | _   | 15.2  | _    | nC   | I <sub>F</sub> = 20A, di/dt = 100A/μs                    |  |

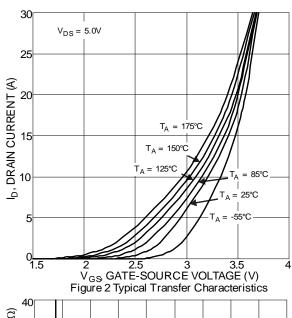
Notes:

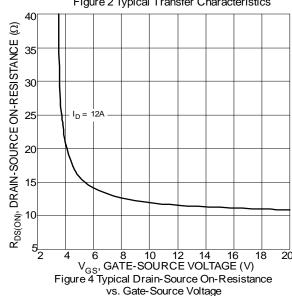
- 5. Device mounted on FR-4 PC board with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

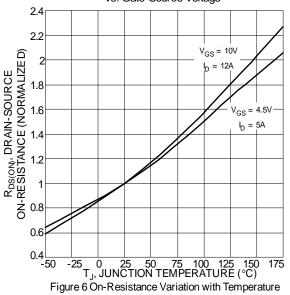




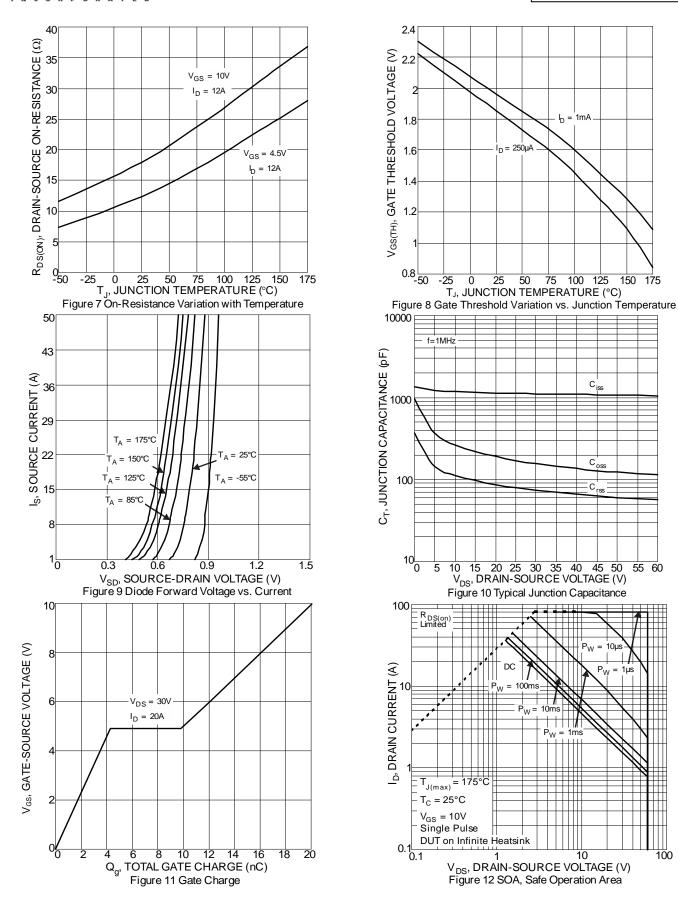






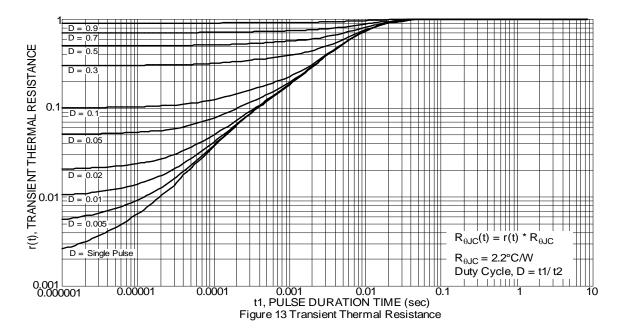






100



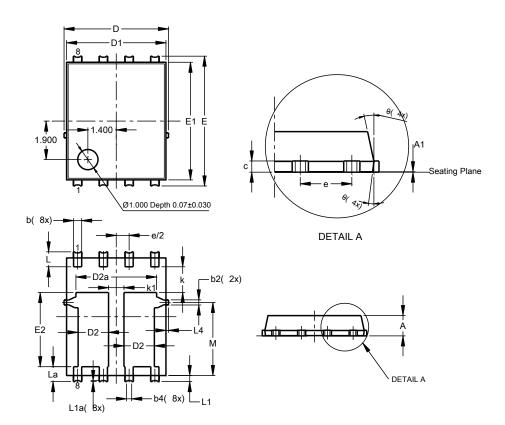




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (SWP) (Type R)

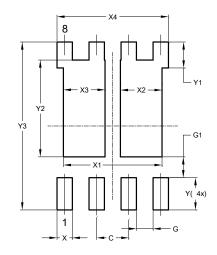


| PowerDI5060-8 (SWP) |                      |         |       |  |  |  |
|---------------------|----------------------|---------|-------|--|--|--|
| (Type R)            |                      |         |       |  |  |  |
| Dim                 | Min Max              |         | Тур   |  |  |  |
| Α                   | 0.90                 | 1.10    | 1.00  |  |  |  |
| A1                  | 0                    | 0.05    |       |  |  |  |
| b                   | 0.30                 | 0.50    | 0.41  |  |  |  |
| b2                  | 0.20                 | 0.35    | 0.25  |  |  |  |
| b4                  |                      | ).25REF | =     |  |  |  |
| С                   | 0.230                | 0.330   | 0.277 |  |  |  |
| D                   | 5                    | .15 BS0 | )     |  |  |  |
| D1                  | 4.70                 | 5.10    | 4.90  |  |  |  |
| D2                  | 1.40                 | 1.60    | 1.50  |  |  |  |
| D2a                 | 3.78 4.18            |         | 3.98  |  |  |  |
| Е                   | 6                    | .40 BS0 | )     |  |  |  |
| E1                  | 5.60                 | 6.00    | 5.80  |  |  |  |
| E2                  | 3.46                 | 3.86    | 3.66  |  |  |  |
| е                   | 1                    | .27BS0  | )     |  |  |  |
| k                   | 1.05                 |         | 1     |  |  |  |
| k1                  | 0.56                 |         |       |  |  |  |
| L                   | 0.635                | 0.835   | 0.735 |  |  |  |
| La                  | 0.635                | 0.835   | 0.735 |  |  |  |
| L1                  | 0.200                | 0.400   | 0.300 |  |  |  |
| L1a                 | 0.050REF             |         |       |  |  |  |
| L4                  | 0.025                | 0.225   | 0.125 |  |  |  |
| М                   | 3.205                | 4.005   | 3.605 |  |  |  |
| θ                   | 10°                  | 12°     | 11°   |  |  |  |
| θ1                  | 6°                   | 8°      | 7°    |  |  |  |
| All                 | All Dimensions in mm |         |       |  |  |  |

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (SWP) (Type R)



| Dimensions | Value   |  |  |
|------------|---------|--|--|
|            | (in mm) |  |  |
| С          | 1.270   |  |  |
| G          | 0.660   |  |  |
| G1         | 0.820   |  |  |
| X          | 0.610   |  |  |
| X1         | 3.910   |  |  |
| X2         | 1.650   |  |  |
| Х3         | 1.650   |  |  |
| X4         | 4.420   |  |  |
| Υ          | 1.270   |  |  |
| Y1         | 1.020   |  |  |
| Y2         | 3.810   |  |  |
| Y3         | 6.610   |  |  |



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